

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3677	(29/832 OR 29/846 OR 29/847).ccls.	USPAT; USOCR	AND	ON	2008/05/01 20:46
L2	5026	(29/832 OR 29/846 OR 29/847).ccls.	US-PGPUB; USPAT; USOCR	AND	ON	2008/05/01 20:48
S1	1	("5919713").pn.	USPAT; USOCR	AND	ON	2007/10/30 10:11
S2	1	("6214639").pn.	USPAT; USOCR	AND	ON	2007/10/30 10:12
S3	1	("5882532").pn.	USPAT; USOCR	AND	ON	2007/10/30 10:13
S4	1	("5597767").pn.	USPAT; USOCR	AND	ON	2007/10/30 10:14
S5	1	("6387778").pn.	USPAT; USOCR	AND	ON	2007/10/30 10:14
S6	4	"0627764"	USPAT; USOCR; EPO; DERWENT	AND	ON	2007/10/30 10:16
S7	0	"0 627 764"	USPAT; USOCR; EPO; DERWENT	AND	ON	2007/10/30 10:19
S8	1100	"strain gage" AND "wheatstone bridge"	USPAT; USOCR	AND	ON	2007/10/30 11:27
S9	1693	"strain gauge" AND "wheatstone bridge"	USPAT; USOCR	AND	ON	2007/10/30 11:28
S10	35	("29"/\$6).ccls. AND "strain gauge" AND "wheatstone bridge"	USPAT; USOCR	AND	ON	2007/10/30 11:30
S11	0	(deformation OR strain) AND sensor AND silicon AND "activatable layer"	USPAT; USOCR	AND	ON	2007/10/30 17:30
S12	12997	(deformation OR strain) AND sensor AND silicon	USPAT; USOCR	AND	ON	2007/10/30 17:30
S13	535	(deformation OR strain) ADJ sensor AND silicon	USPAT; USOCR	AND	ON	2007/10/30 17:30
S14	98	(deformation OR strain) ADJ sensor AND silicon AND "wheatstone bridge"	USPAT; USOCR	AND	ON	2007/10/30 17:31

S15	0	silicon AND "sacrificial layer" and "activatable layer"	USPAT; USOCR	AND	ON	2007/10/30 17:43
S16	6047	silicon AND "sacrificial layer"	USPAT; USOCR	AND	ON	2007/10/30 17:44
S17	10	silicon AND "sacrificial layer" AND activat\$6 ADJ layer	USPAT; USOCR	AND	ON	2007/10/30 17:44
S18	2	("6117701" "6287885").PN.	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 17:49
S19	11	("4808549" "5162251" "5217916" "5219796" "5279975" "5331454" "5358590" "5393706" "5418190" "5435876" "5445559").PN.	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:12
S20	3	("4808549" "5162251" "5217916" "5219796" "5279975" "5331454" "5358590" "5393706" "5418190" "5435876" "5445559").PN. AND hold	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:14
S21	38	semiconductor AND (chip SAME hold SAME transfer SAME carrier)	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:41
S22	2	semiconductor AND (chip SAME hold SAME saw SAME transfer SAME carrier)	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:47
S23	1	wafer AND (chip SAME hold SAME saw SAME transfer SAME carrier)	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:49
S24	5	wafer AND (hold SAME saw SAME transfer SAME carrier)	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:50
S25	6	semiconductor AND (hold SAME saw SAME transfer SAME carrier)	US-PGPUB; USPAT; USOCR	AND	ON	2007/10/30 18:50
S26	13	semiconductor AND ("holding device" SAME chip SAME carrier)	USPAT; USOCR	AND	ON	2007/10/30 19:13

S27	0	semiconductor AND (transfer WITH chip WITH "holding device" WITH carrier)	USPAT; USOCR	AND	ON	2007/10/30 19:28
S28	8	semiconductor AND (transfer WITH chip WITH hold\$4 WITH carrier)	USPAT; USOCR	AND	ON	2007/10/30 19:28
S29	1	("5435876").pn.	USPAT; USOCR	AND	ON	2007/10/30 19:39
S30	5003	semiconductor AND "sacrificial layer"	USPAT; USOCR	AND	ON	2007/10/31 09:34
S31	3	semiconductor AND "sacrificial layer" SAME "activation layer"	USPAT; USOCR	AND	ON	2007/10/31 09:34
S32	3	semiconductor AND "sacrificial layer" SAME (activa\$6 ADJ layer)	USPAT; USOCR	AND	ON	2007/10/31 09:36
S33	165	("29"/\$6).ccls. AND semiconductor AND "sacrificial layer"	USPAT; USOCR	AND	ON	2007/10/31 09:37
S34	35	("29"/\$6).ccls. AND semiconductor AND "sacrificial layer" AND sensitive	USPAT; USOCR	AND	ON	2007/10/31 09:39
S35	312	semiconductor AND silicon AND (deformation OR strain) ADJ sensor	USPAT; USOCR	AND	ON	2007/10/31 10:23
S36	1	("6407764").pn.	USPAT; USOCR	AND	ON	2007/10/31 14:05
S37	4	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND oxide	USPAT; USOCR	AND	ON	2007/10/31 14:12

S38	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND "silicon oxide"	USPAT; USOCR	AND	ON	2007/10/31 14:12
S39	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND polycrystalline	USPAT; USOCR	AND	ON	2007/10/31 14:14
S40	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND monocrystalline	USPAT; USOCR	AND	ON	2007/10/31 14:15
S41	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND monocrystalline	USPAT; USOCR	AND	ON	2007/10/31 14:15

S42	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND polycrystalline	USPAT; USOCR	AND	ON	2007/10/31 14:15
S43	0	("5882532" OR "5919713" OR "6214639" OR "5597767" OR "6387778" OR "4620365" OR "5209120" OR "5507090" OR "6148662" OR "5680746" OR "6332359" OR "6407764").pn. AND polycrystalline	USPAT; USOCR	AND	ON	2007/10/31 14:15
S44	0	semiconductor.ti. AND ("silicon oxide on") NEAR5 substrate	USPAT; USOCR	AND	ON	2007/10/31 14:17
S45	5415	semiconductor.ti. AND ("silicon oxide") NEAR5 substrate	USPAT; USOCR	AND	ON	2007/10/31 14:17
S46	3349	semiconductor.ti. AND ("silicon oxide") NEAR3 substrate	USPAT; USOCR	AND	ON	2007/10/31 14:18
S47	2058	semiconductor.ti. AND ("silicon oxide") NEAR2 substrate	USPAT; USOCR	AND	ON	2007/10/31 14:18
S48	0	semiconductor.ti. AND ("silicon oxide on the substrate")	USPAT; USOCR	AND	ON	2007/10/31 14:19
S49	233	semiconductor.ti. AND ("silicon oxide") NEAR5 substrate WITH "polycrystalline silicon"	USPAT; USOCR	AND	ON	2007/10/31 14:21
S50	1	("6407764").pn. AND sacrificial WITH etch\$4	USPAT; USOCR	AND	ON	2007/10/31 17:48
S51	1	("6407764").pn. AND etch\$4 WITH wear	USPAT; USOCR	AND	ON	2007/10/31 17:53

S52	73	semiconductor AND "vacuum gripper"	USPAT; USOCR	AND	ON	2007/10/31 19:35
S53	4	semiconductor AND "vacuum gripper" SAME carrier	USPAT; USOCR	AND	ON	2007/10/31 19:36
S54	0	semiconductor AND "vacuum gripper" SAME carrier SAME clamp\$3	USPAT; USOCR	AND	ON	2007/10/31 19:47
S55	9	semiconductor AND "vacuum gripper" SAME clamp\$4 AND carrier	USPAT; USOCR	AND	ON	2007/10/31 19:47
S56	15	semiconductor AND "electrostatic clamping device"	USPAT; USOCR	AND	ON	2007/10/31 19:48
S57	1001	(29/592.1).ccls.	USPAT; USOCR	AND	ON	2007/11/09 21:48
S58	225	(29/595).ccls.	USPAT; USOCR	AND	ON	2007/11/09 21:49
S59	1392	(29/825).ccls.	USPAT; USOCR	AND	ON	2007/11/09 21:50
S60	1429	(29/825).ccls.	USPAT; USOCR	AND	ON	2008/05/01 17:06
S61	1035	(29/592.1).ccls.	USPAT; USOCR	AND	ON	2008/05/01 17:12
S62	236	(29/595).ccls.	USPAT; USOCR	AND	ON	2008/05/01 17:15
S63	277	(29/825).ccls.	US-PGPUB	AND	ON	2008/05/01 17:19
S64	326	(29/592.1).ccls.	US-PGPUB	AND	ON	2008/05/01 17:22
S65	90	(29/595).ccls.	US-PGPUB	AND	ON	2008/05/01 17:24
S66	68	("257"/\$6).ccls. and (etch\$3 with (around OR perimeter OR circumference) with circuit)	US-PGPUB	AND	ON	2008/05/01 17:30

5/1/2008 9:52:21 PM

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